

SILICON POWER TRANSISTOR 2SA1395

PNP SILICON EPITAXIAL TRANSISTOR FOR HIGH-SPEED SWITCHING

The 2SA1395 is a mold power transistor developed for highspeed switching, and is ideal for use as a driver in devices such as switching regulators, DC/DC converters, and high-frequency power amplifiers.

FEATURES

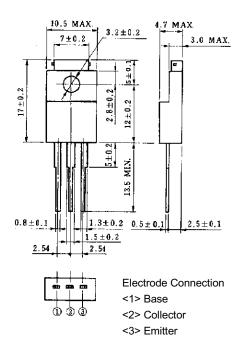
- Mold package that does not require an insulating board or insulation bushing
- Low collector saturation voltage: V_{CE(sat)} = -0.6 V MAX. (@-1 A)
- Fast switching speed: $t_f = 0.5 \mu s MAX. (@-1 A)$
- Complementary transistor: 2SC3567

ABSOLUTE MAXIMUM RATINGS (Ta = 25°C)

Parameter	Symbol	Ratings	Unit
Collector to base voltage	Vcво	-100	V
Collector to emitter voltage	VCEO	-100	V
Emitter to base voltage	VEBO	-7.0	V
Collector current (DC)	Ic(DC)	-2.0	Α
Collector current (pulse)	IC(pulse)*	-4.0	Α
Base current (DC)	I _{B(DC)}	-1.0	Α
Total power dissipation	P⊤ (Tc = 25 °C)	15	W
Total power dissipation	P⊤ (Ta = 25 °C)	2.0	W
Junction temperature	Tj	150	°C
Storage temperature	Tstg	_55 to +150	°C

^{*} PW \leq 300 μ s, duty cycle \leq 10%

PACKAGE DRAWING (UNIT: mm)



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ELECTRICAL CHARACTERISTICS (Ta = 25°C)

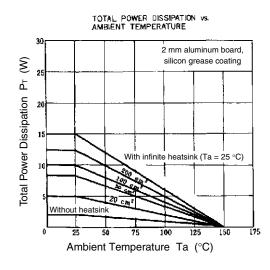
Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Collector to emitter voltage	VCEO(SUS)	Ic = -1.0 A, I _{B1} = -0.1 A, L = 1 mH	-100			٧
Collector to emitter voltage	VCEX(SUS)1	$I_{C} = -1.0 \text{ A}, \ I_{B1} = -I_{B2} = -0.1 \text{ A},$ $V_{BE(OFF)} = 5.0 \text{ V}, \ L = 180 \ \mu\text{H}, \ clamped$	-100			V
Collector to emitter voltage	VCEX(SUS)2	$I_{C} = -2.0 \text{ A}, \ I_{B1} = -0.2 \text{ A}, \ I_{B2} = 0.1 \text{ A}, \ V_{BE(OFF)} = 5.0 \text{ V}, \ L = 180 \ \mu\text{H}, \ clamped$	-100			V
Collector cutoff current	Ісво	V _{CB} = -100 V, I _E = 0			-10	μΑ
Collector cutoff current	ICER	$V_{\text{CE}} = -100 \text{ V}, \text{ R}_{\text{BE}} = 51 \Omega, \text{ Ta} = 125^{\circ}\text{C}$			-1.0	mA
Collector cutoff current	ICEX1	$V_{CE} = -100 \text{ V}, V_{BE(OFF)} = 5.0 \text{ V}$			-10	μΑ
Collector cutoff current	ICEX2	$V_{CE} = -100 \text{ V}, V_{BE(OFF)} = 5.0 \text{ V},$ $Ta = 125^{\circ}C$			-1.0	mA
Emitter cutoff current	ІЕВО	V _{EB} = -5.0 V, I _C = 0			-10	μΑ
DC current gain	h _{FE1} *	VcE = -5.0 V, Ic = -0.1 A	40			
DC current gain	h _{FE2} *	VcE = -5.0 V, Ic = -1.0 A	40		200	
Collector saturation voltage	V _{CE(sat)} *	Ic = -1.0 A, I _B = -0.1 A			-0.6	٧
Base saturation voltage	V _{BE(sat)} *	$I_C = -1.0 \text{ A}, I_B = -0.1 \text{ A}$			-1.5	٧
Turn-on time	ton	$I_{C} = -1.0 \text{ A}, R_{L} = 50 \Omega,$			0.5	μs
Storage time	tstg	$I_{B1} = -I_{B2} = -0.1 \text{ A}, \text{ Vcc} \cong -50 \text{ V}$ Refer to the test circuit.			1.5	μs
Fall time	tf	nelei to the test choult.			0.5	μs

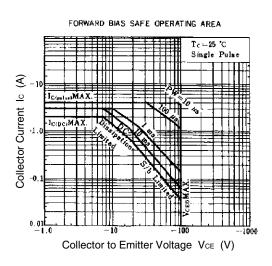
^{*} Pulse test PW \leq 350 μ s, duty cycle \leq 2%

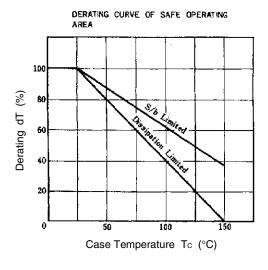
hfe CLASSIFICATION

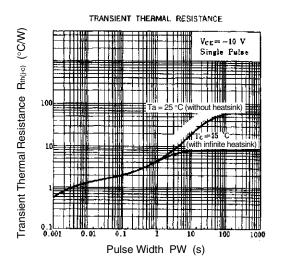
Marking	М	L	Κ
h _{FE2}	40 to 80	60 to 120	100 to 200

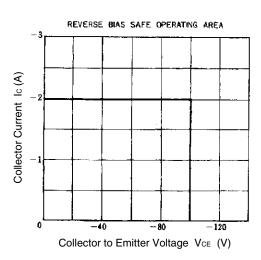
TYPICAL CHARACTERISTICS (Ta = 25 °C)

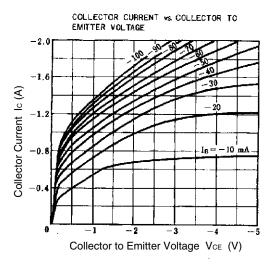


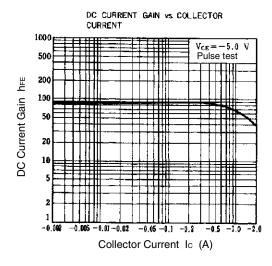


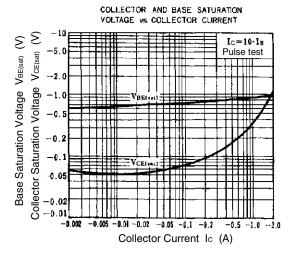






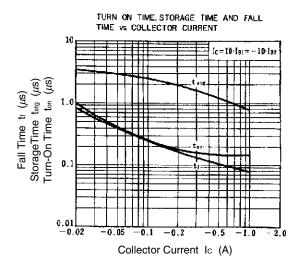




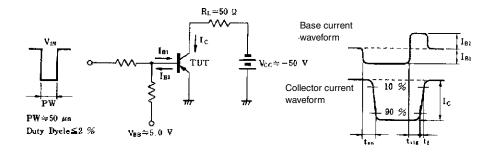


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SWITCHING TIME (ton, tstg, tf) TEST CIRCUIT





[MEMO]

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